

# ICEM Modeling of Microcontroller current activity

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The principle of this method consists in determining the internal current activity directly from the measurement of the external current. The method is summarized in the figure 1.

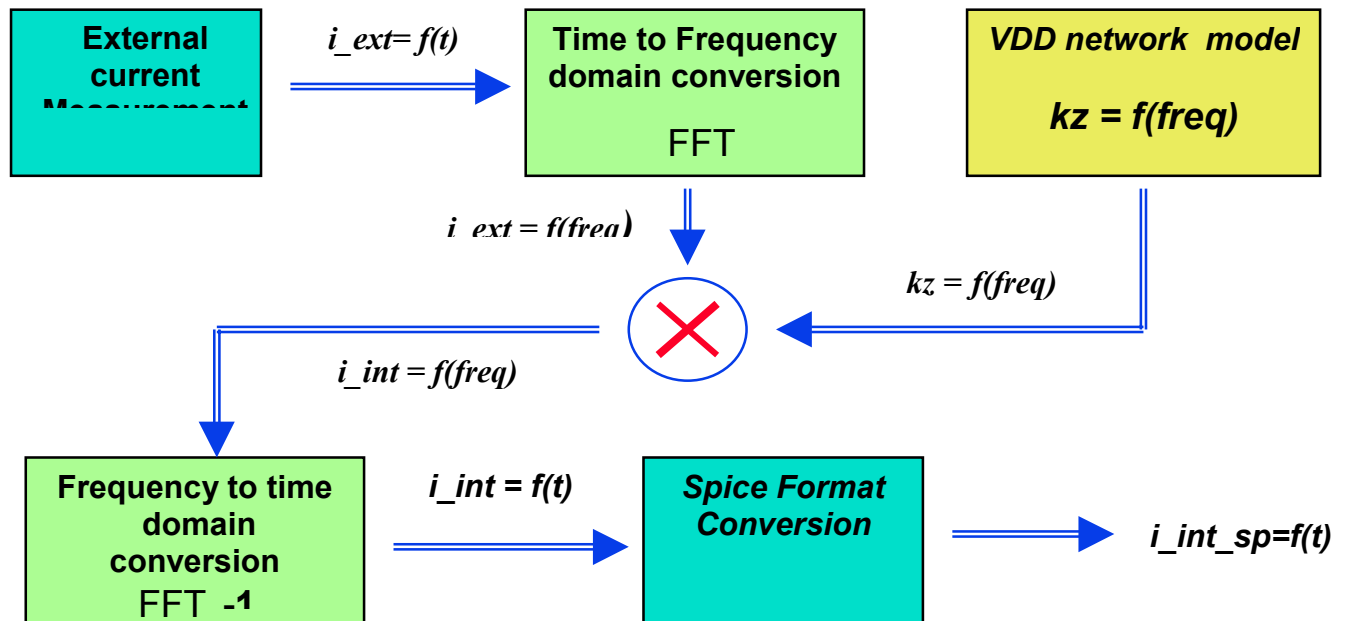


Figure 1 Modeling method

The electrical circuit used for the Spice simulation is given in figure 2.

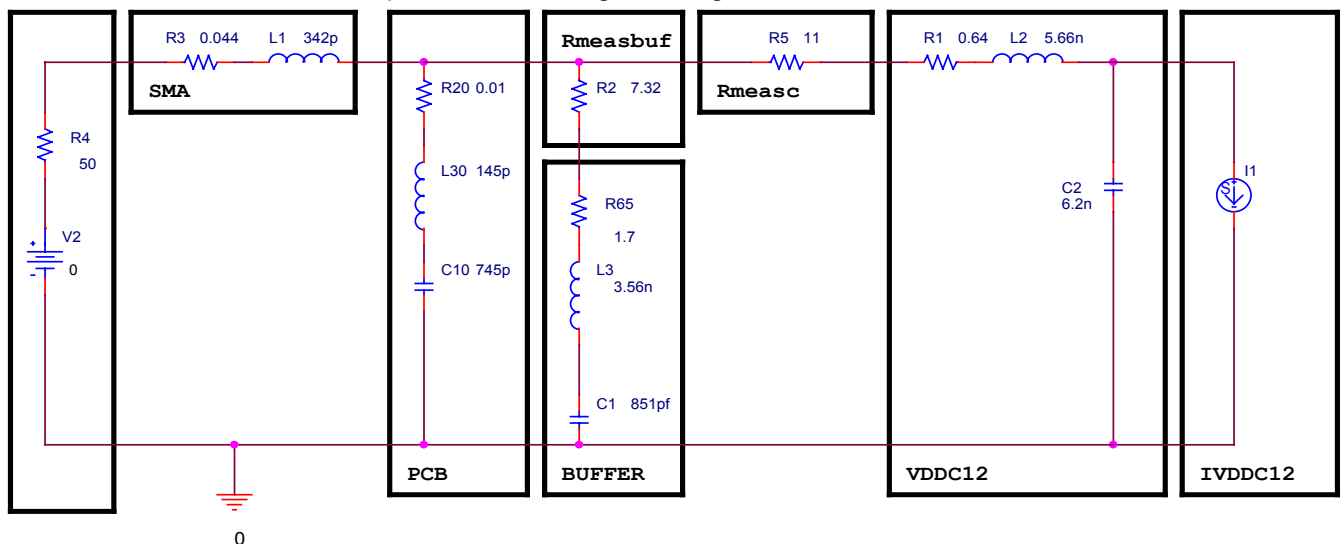


Figure 2. Spice model for extracting the current model of the microcontroller core.

Figure 3 compares simulated and measured results. The microcontroller is maintained under reset state. The current measured across the Rmeasc resistor,  $I_{ext}$ , is plotted in red and is simulated in green.

There is a good correlation with a little offset due to the computing noise of the FFT and FFT-1.

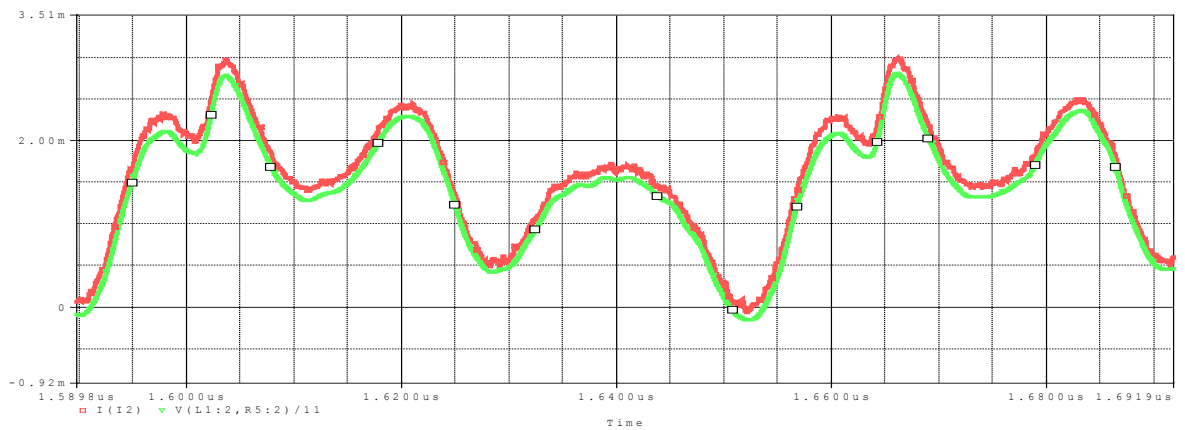


Figure 3. Plot of the  $i_{ext}$  current: Red measurement, Green simulation.

Figure 4. plots  $i_{int}$  (red) computed by the method described in figure1. This plot shows some current pics due to the internal activity of the microcontroller and synchronised to the clock.

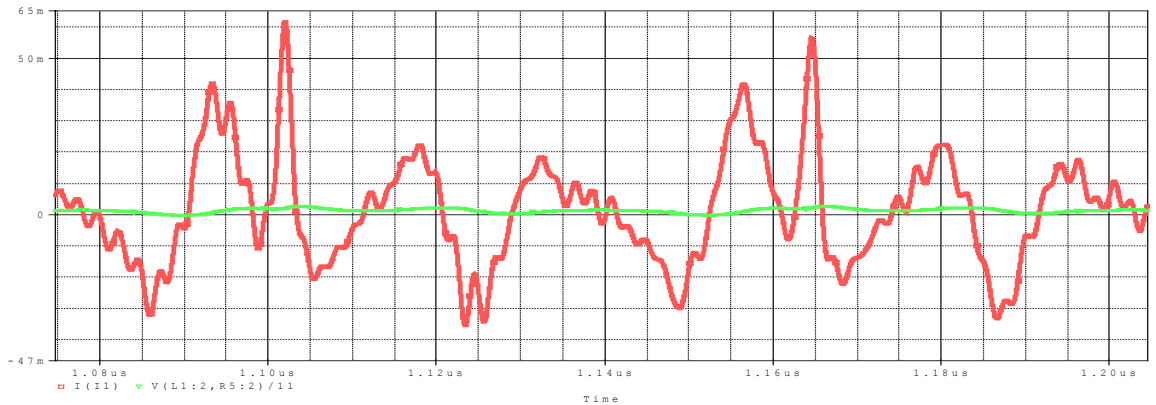


Figure 4. Plot of  $i_{int}$  current in Red and  $i_{ext}$  in green.

Figure 5 shows the electrical schematic used to predict the current  $i_{ext}$  across the Rmeasbuf.

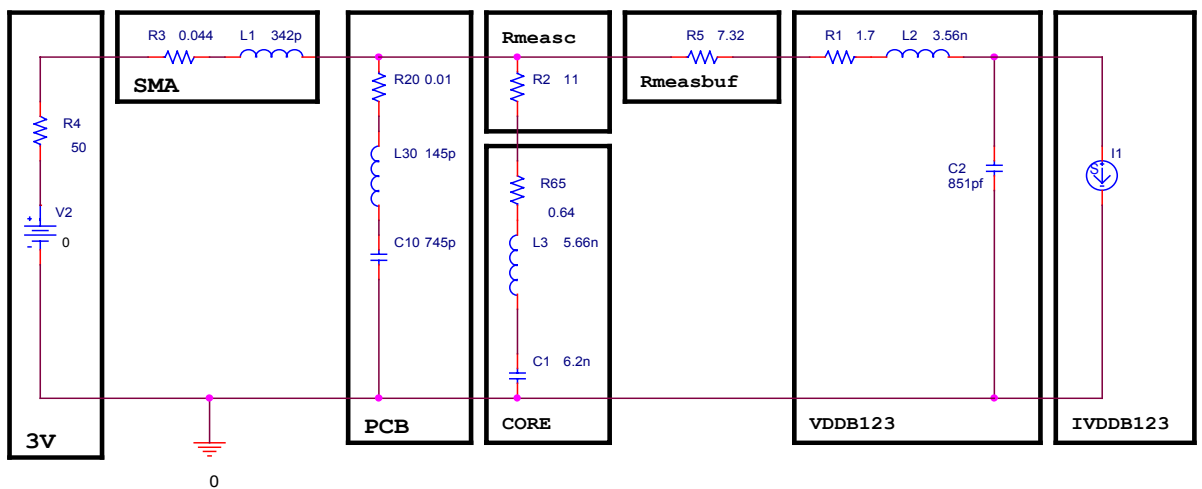


Figure 5. Electrical schematic for predicting the  $i_{ext}$  of the buffer.

Figure 6 shows the correlation between the measurement and the simulation of  $i_{ext}$ . There is a very good correlation between both traces.

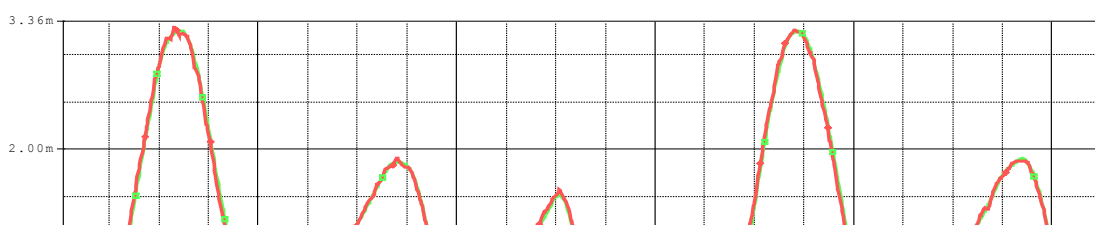


Figure 6.  $i_{ext}$ , measurement in red and simulation in green.

Figure 7 plots the  $i_{int}$  current computed with the method described in figure1 and  $I_{ext}$  current measured across the Rmeasbuf.

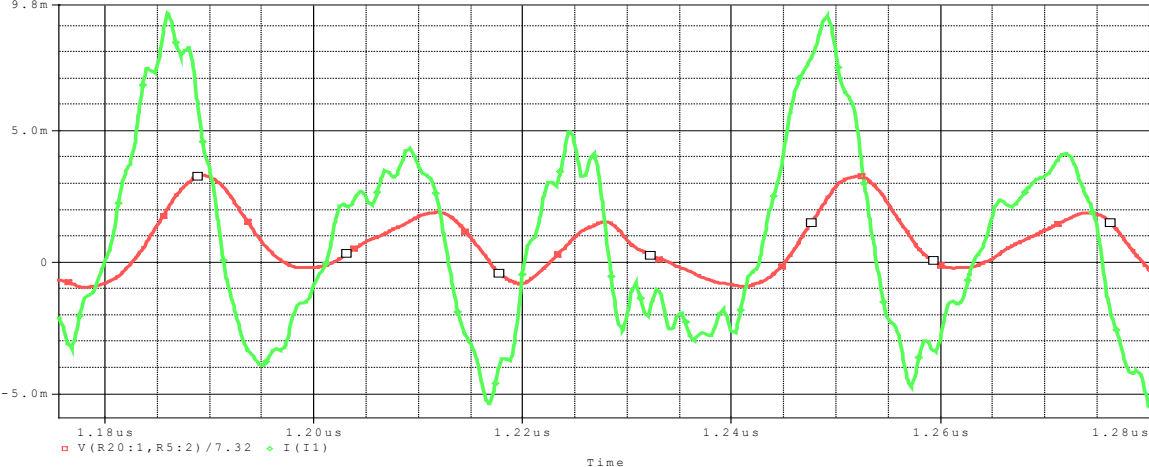


Figure 7  $i_{int}$  in green,  $i_{ext}$  in red.

These first results shows the accuracy of the modelling method which allows to isolate the current activity of the silicon alone.